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ATTORNEY DOCKET MIT8288CON

Kim et al.
APPLICANT

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FILING DATE

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GROUP

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EXAMINER

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA	6,064,076	5/16/00	Chen et al.			5/20/98
	AB	4,378,259	03/29/83	Hasegawa et al.			12/24/80
	AC	4,680,602	July, 1987	Watanabe et al.	357	17	
	AD	4,218,270	July, 1987	Hasegawa et al.			
	AE						
	AF						
	AG						
	AH						

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	AI	19756856	7/2/98	Germany			No
	AJ	54-146984	11/1979	Japan			
	AK	06*-061,525	11/1979	Japan			
	AL						
	AM						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
	AN	Chin, T.P., J.C.P. Chang, K.L. Kavanagh and C.W. Tu, "Gas-source molecular beam epitaxial growth, characterization, and light-emitting diode application of $\text{In}_x\text{Ga}_{1-x}\text{P}$ on GaP(100)," <u>Applied Physics Letters</u> , vol. 62, no. 19, May 10, 1993, pp. 2369-2371.
	AO	Kim, A.Y. and E.A. Fitzgerald, "Engineering Dislocation Dynamics in $\text{In}_x(\text{Al}_y\text{Ga}_{1-y})_{1-x}\text{P}$ Graded Buffers on GaP by MOVPE," presented at the Defect and Impurity Engineered Semiconductors II Symposium, San Francisco, California, April 13-17, 1998, published in Materials Research Society Symposium Proceedings vol. 510, pp. 131-135.

EXAMINER

DATE CONSIDERED 9/28/00

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Initial if citation considered, with the reference citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.